
PF0410

MOS FET Power Amplifier Module for DSC1800 Handy Phone

HITACHI

ADE-208-324B (Z)
3rd. Edition
July 1996

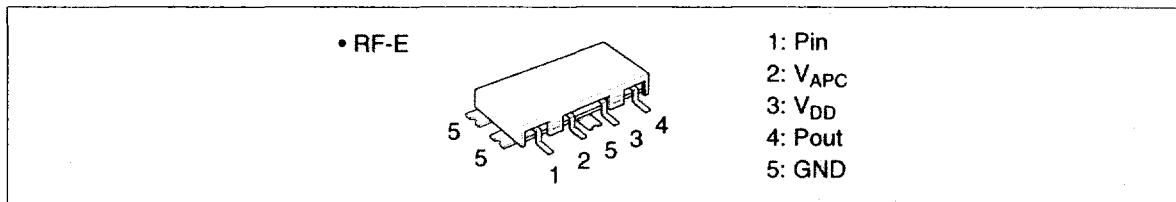
Application

For DCS 1800 class 1: 1710 to 1785 MHz

Features

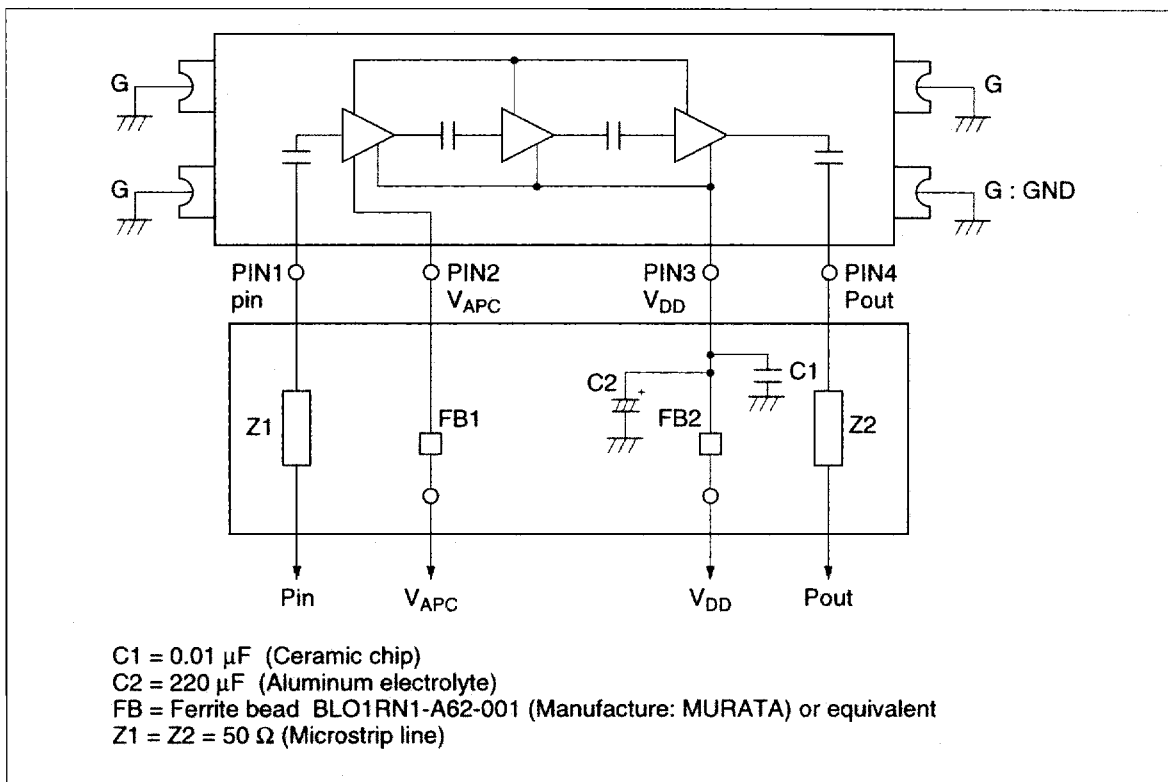
- Small package: 1 cc, 3g
- High efficiency: 35% Typ
- High speed switching: 0.9 μ sec

Pin Arrangement



PF0410

Internal Diagram and External Circuit



Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

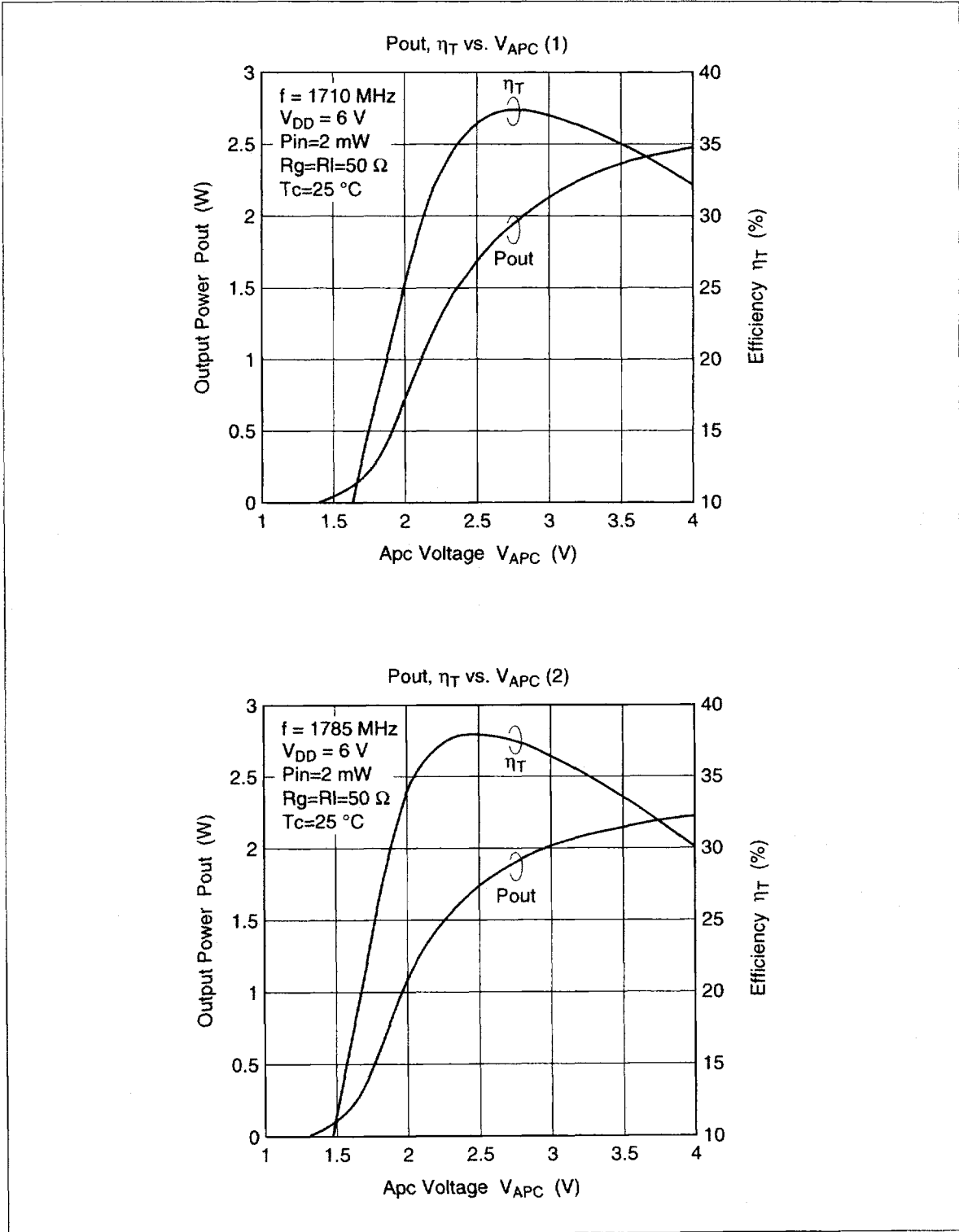
Item	Symbol	Rating	Unit
Supply voltage	VDD	10	V
Supply current	IDD	2	A
VAPC voltage	VAPC	6	V
Input power	Pin	20	mW
Operating case temperature	T_c (op)	-30 to +100	$^\circ\text{C}$
Storage temperature	T_{stg}	-30 to +100	$^\circ\text{C}$
Output power	Pout	3	W

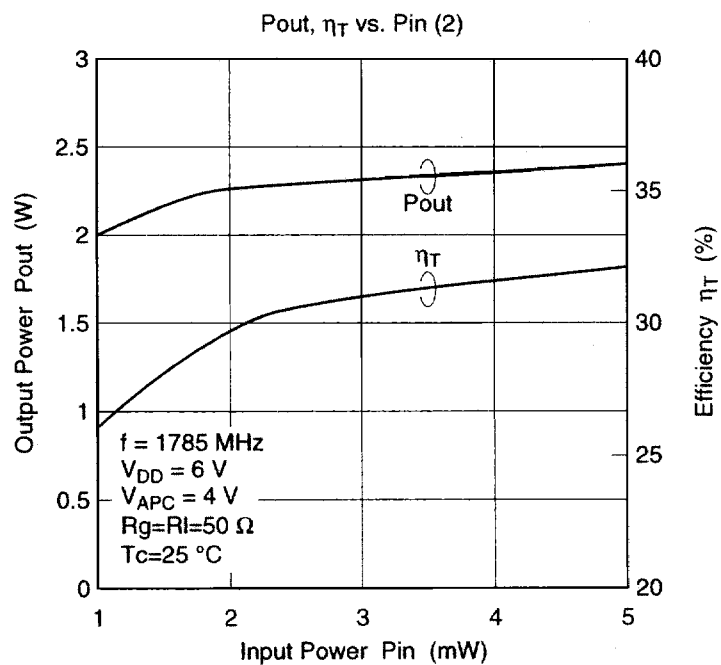
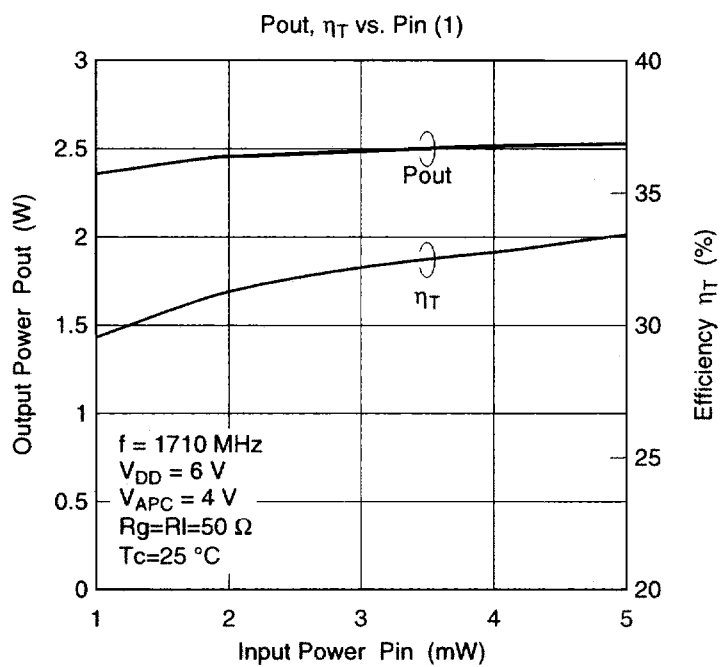
Electrical Characteristics (T_c = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	1710	—	1785	MHz	—
Control Voltage range	VAPC	0.5	—	4.0	V	—
Drain cutoff current	I _{DS}	—	—	100	μA	VDD = 10 V, VAPC = 0 V
Total efficiency	η _T	30	35	—	%	Pin = 2 mW, VDD = 6 V,
2nd harmonic distortion	2nd H.D.	—	-50	-30	dBc	Pout = 1.6 W (at APC controlled),
3rd harmonic distortion	3rd H.D.	—	-50	-30	dBc	RL = Rg = 50 Ω, Tc = 25°C
Input VSWR	VSWR (in)	—	2	3	—	
Output power (1)	Pout (1)	2.0	2.5	—	W	Pin = 2 mW, VDD = 6 V, VAPC = 4 V RL = Rg = 50 Ω, Tc = 25°C
Output power (2)	Pout (2)	1.2	1.5	—	W	Pin = 2 mW, VDD = 5.4 V, VAPC = 4 V RL = Rg = 50 Ω, Tc = 80°C
Isolation	—	—	-35	-30	dBm	Pin = 2 mW, VDD = 6 V, VAPC = 0.5 V, RL = Rg = 50 Ω
Switching time	tr, tf	—	-0.9	2	μs	Pin = 2 mW, VDD = 6 V, Pout = 1.6 W, RL = Rg = 50 Ω, Tc = 25°C
Stability	—	No parasitic			—	Pin = 2 mW, VDD = 7.5 V, Pout ≤ 1.6 W, (at APC controlled), Rg = 50 Ω, Tc = 25°C Output VSWR = 10:1 All phases

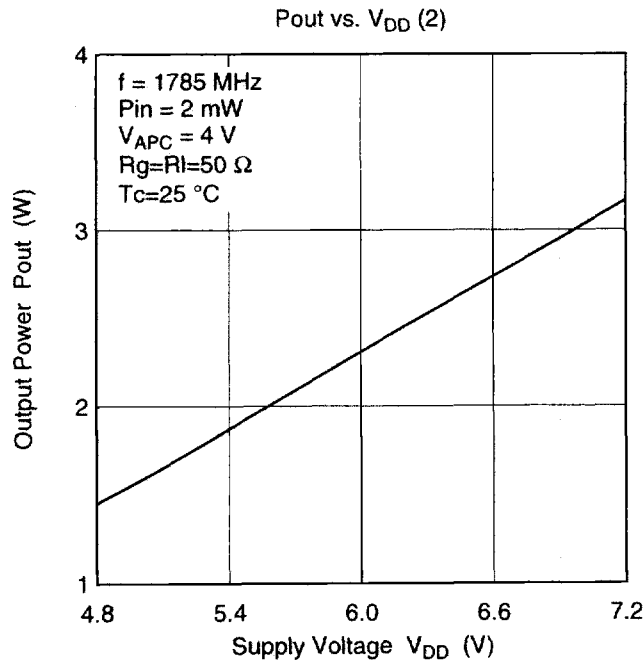
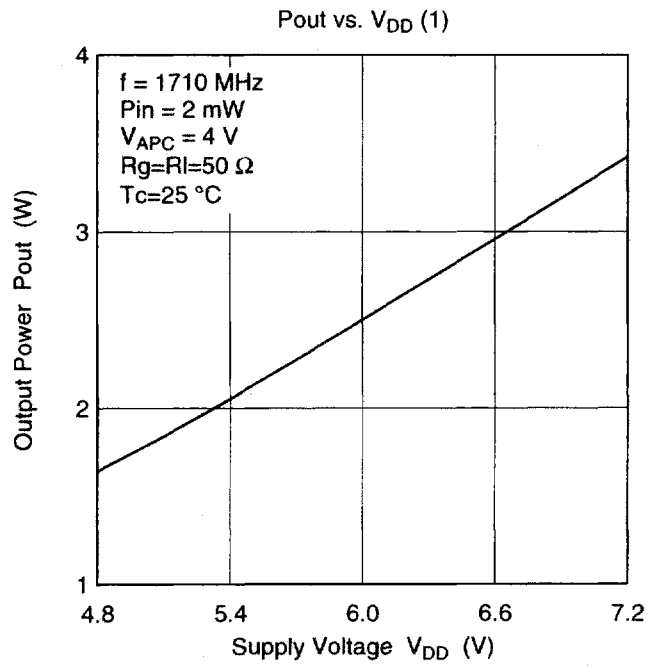
PF0410

Characteristics Curve

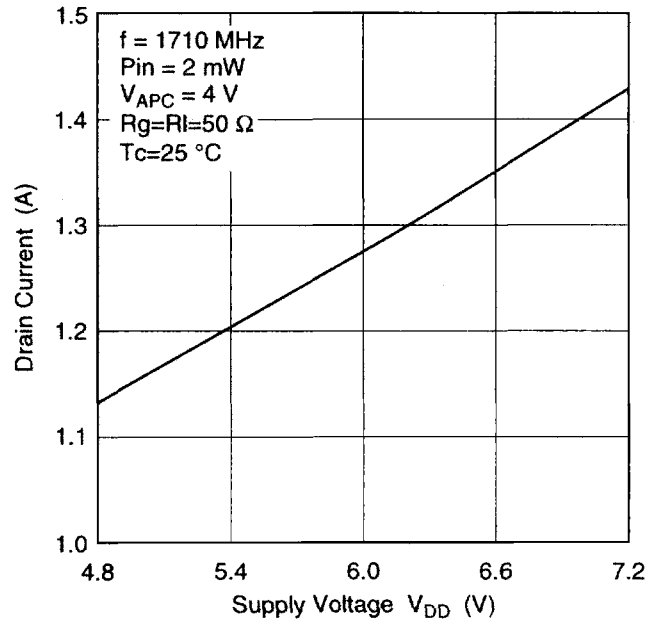




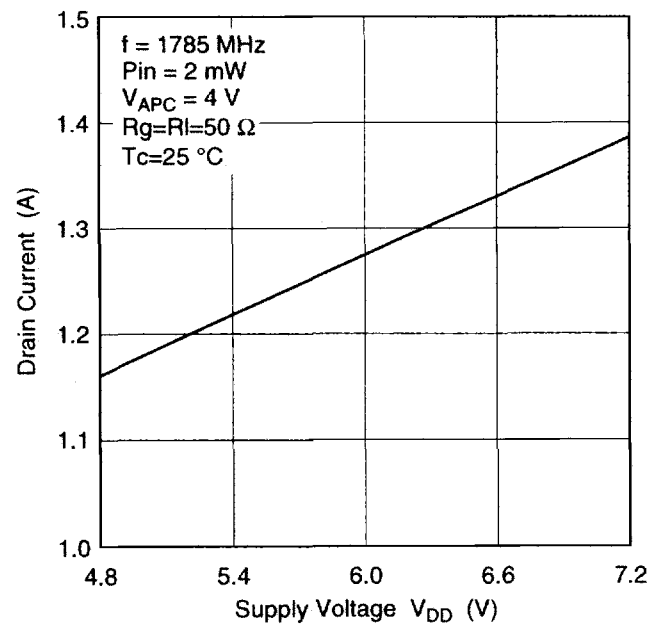
PF0410



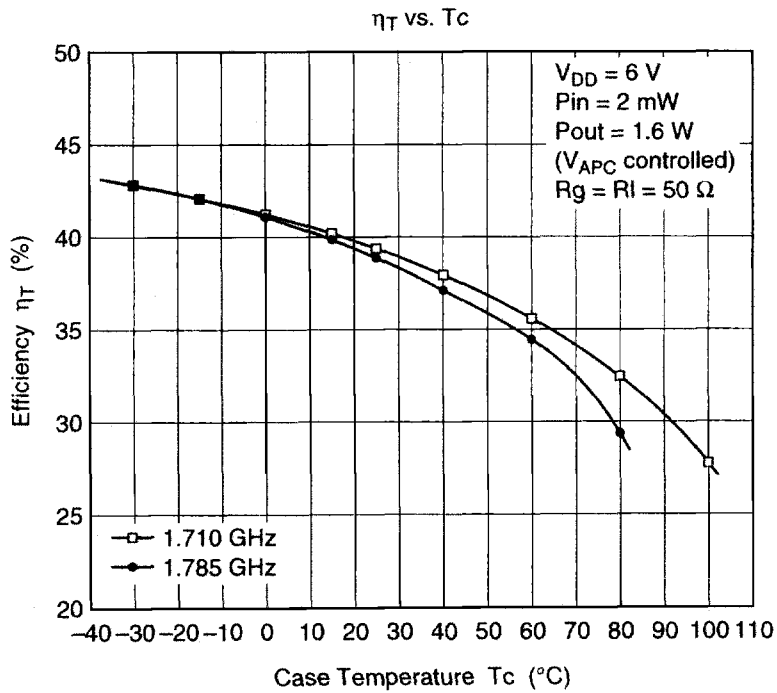
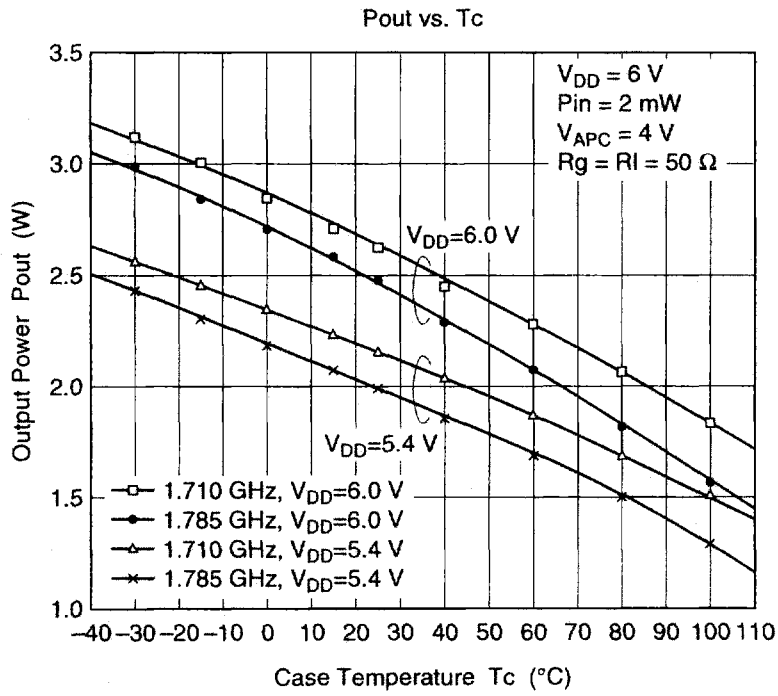
Drain Current vs. V_{DD} (1)



Drain Current vs. V_{DD} (2)



PF0410



Package Dimensions

Unit: mm

